AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Previously presented) A semiconductor light-emitting device comprising:

a DBR (Distributed Bragg Reflector) and a light-emitting layer supported by at least a substrate comprising GaAs, the DBR being located between the substrate comprising GaAs and the light-emitting layer, wherein light directed from the light-emitting layer toward a top surface of the light-emitting device has a radiation angle dependence;

a semiconductor layer formed over at least the light-emitting layer, a top surface of the semiconductor layer comprising a roughened surface which is not at least partially covered by the other semiconductor layers in order to cause light output from the light-emitting device to be diffused upon leaving the top surface of the device; and

wherein no DBR is provided between the light-emitting layer and the semiconductor layer having the top surface that is roughened.

2. (Original) The semiconductor light-emitting device according to claim 1, wherein the light-emitting layer to be formed on the GaAs substrate is a single layer or a plurality of layers made of $Al_yGa_zIn_{1-y-z}P$ ($0 \leq y \leq 1$, $0 \leq z \leq 1$).

3. (Original) The semiconductor light-emitting device according to claim 1, wherein the semiconductor layer whose top surface is a roughened surface is made of $Al_xGa_{1-x}As$ ($0 \leq x \leq 1$).

4. (Original) The semiconductor light-emitting device according to claim 3, wherein the semiconductor layer made of $Al_xGa_{1-x}As$ ($0 \leq x \leq 1$) is transparent to an emission wavelength.

5. (Original) The semiconductor light-emitting device according to claim 3, wherein the semiconductor layer made of $Al_xGa_{1-x}As$ ($0 \leq x \leq 1$) has an Al mixed crystal ratio x of 0.5 - 0.8.

6. (Original) The semiconductor light-emitting device according to claim 3, further comprising an $Al_yGa_zIn_{1-y-z}P$ ($0 \leq y \leq 1$, $0 \leq z \leq 1$) layer for diffusing a current injected from an electrode provided on a light takeout side, the $Al_yGa_zIn_{1-y-z}P$ layer being provided between the semiconductor layer made of $Al_xGa_{1-x}As$ ($0 \leq x \leq 1$) and the light-emitting layer.

7. (Original) The semiconductor light-emitting device according to claim 1, wherein the layer whose top surface is a roughened surface is made of $Al_yGa_zIn_{1-y-z}P$ ($0 \leq y \leq 1$, $0 \leq z \leq 1$).

8. (Original) The semiconductor light-emitting device according to claim 7, wherein the layer whose top surface is a roughened surface has a lattice constant different by 0.5% or more from that of the GaAs substrate.

9-14. (Canceled)

15. (Previously presented) A semiconductor light-emitting device comprising:

a DBR (Distributed Bragg Reflector) and a light-emitting layer supported by a substrate comprising GaAs, the DBR being located closer to the substrate comprising GaAs than is the light-emitting layer; and

a semiconductor layer formed on the light-emitting layer, and wherein at least part of a top surface of the semiconductor layer is roughened so as to define a roughened surface which is not at least partially covered by the other semiconductor layers in order to cause light output from the light-emitting device to be diffused upon leaving the top surface of the device; and

wherein no DBR is provided between the light-emitting layer and the semiconductor layer having the top surface that is roughened.

16. (Previously presented) The semiconductor light-emitting device according to claim 15, wherein the light-emitting layer is a single layer or a plurality of layers comprising $Al_yGa_zIn_{1-y-z}P$ ($0 \leq y \leq 1$, $0 \leq z \leq 1$).

17. (Previously presented) The semiconductor light-emitting device according to claim 15, wherein the semiconductor layer whose top surface is a roughened surface comprises $Al_xGa_{1-x}As$ ($0 \leq x \leq 1$).

18. (Previously presented) The semiconductor light-emitting device according to Claim 17, wherein the semiconductor layer comprising $Al_xGa_{1-x}As$ ($0 \leq x \leq 1$) is transparent to an emission wavelength.

19. (Previously presented) The device of claim 15, further comprising a current diffusion layer located between at least the light-emitting layer and the semiconductor having the top surface that is roughened, and an etch stop layer provided between the current diffusion layer and said semiconductor layer having the top surface that is roughened.

20. (Previously presented) The device of claim 15, wherein the device includes only one DBR.

21. (New) The light-emitting device of claim 1, wherein the semiconductor with roughened surface has a lattice constant different by 0.5% or more than that of the substrate comprising GaAs.

22. (New) The light-emitting device of claim 15, wherein the semiconductor with roughened surface has a lattice constant different by 0.5% or more than that of the substrate comprising GaAs.

23. (New) The light-emitting device of claim 1, wherein a top electrode of the device includes a plurality of separate apertures defined therein so as to expose different parts of the roughened surface of the semiconductor layer.

24. (New) The light-emitting device of claim 15, wherein a top electrode of the device includes a plurality of separate apertures defined therein so as to expose different parts of the roughened surface of the semiconductor layer.

25. (New) The light-emitting device of claim 1, wherein no mirror/reflector is provided between the light-emitting layer and the semiconductor layer having the top surface that is roughened.

26. (New) The light-emitting device of claim 15, wherein no mirror/reflector is provided between the light-emitting layer and the semiconductor layer having the top surface that is roughened.